GD313x/GD312x Advanced High Voltage Isolated Gate Driver

GD313X-GD312X NEW

Preproduction

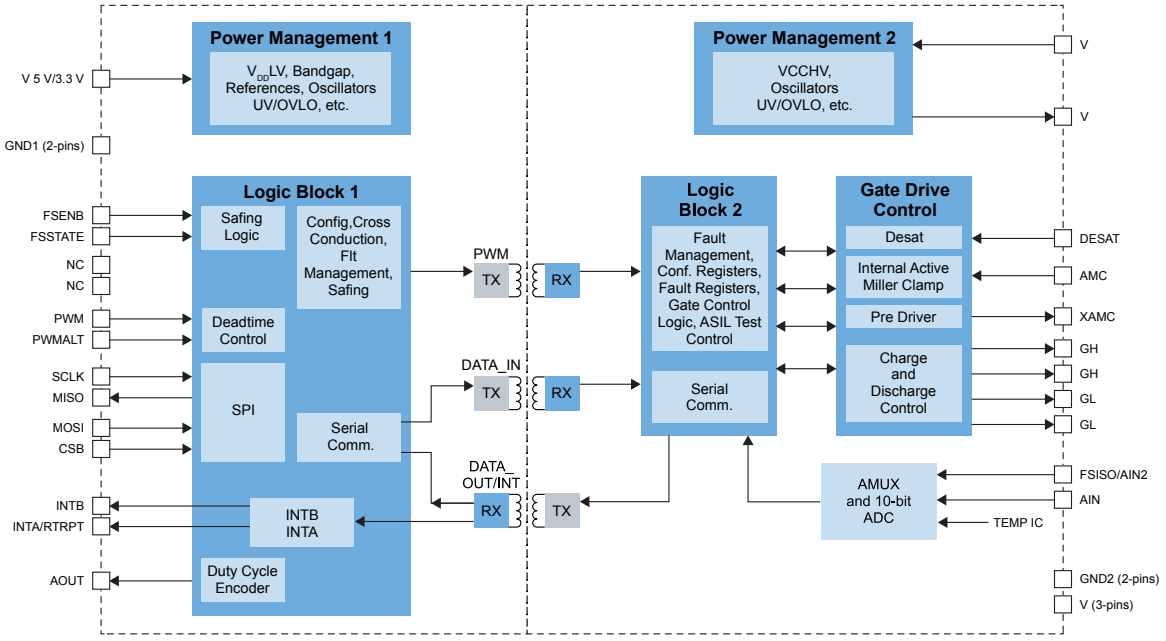
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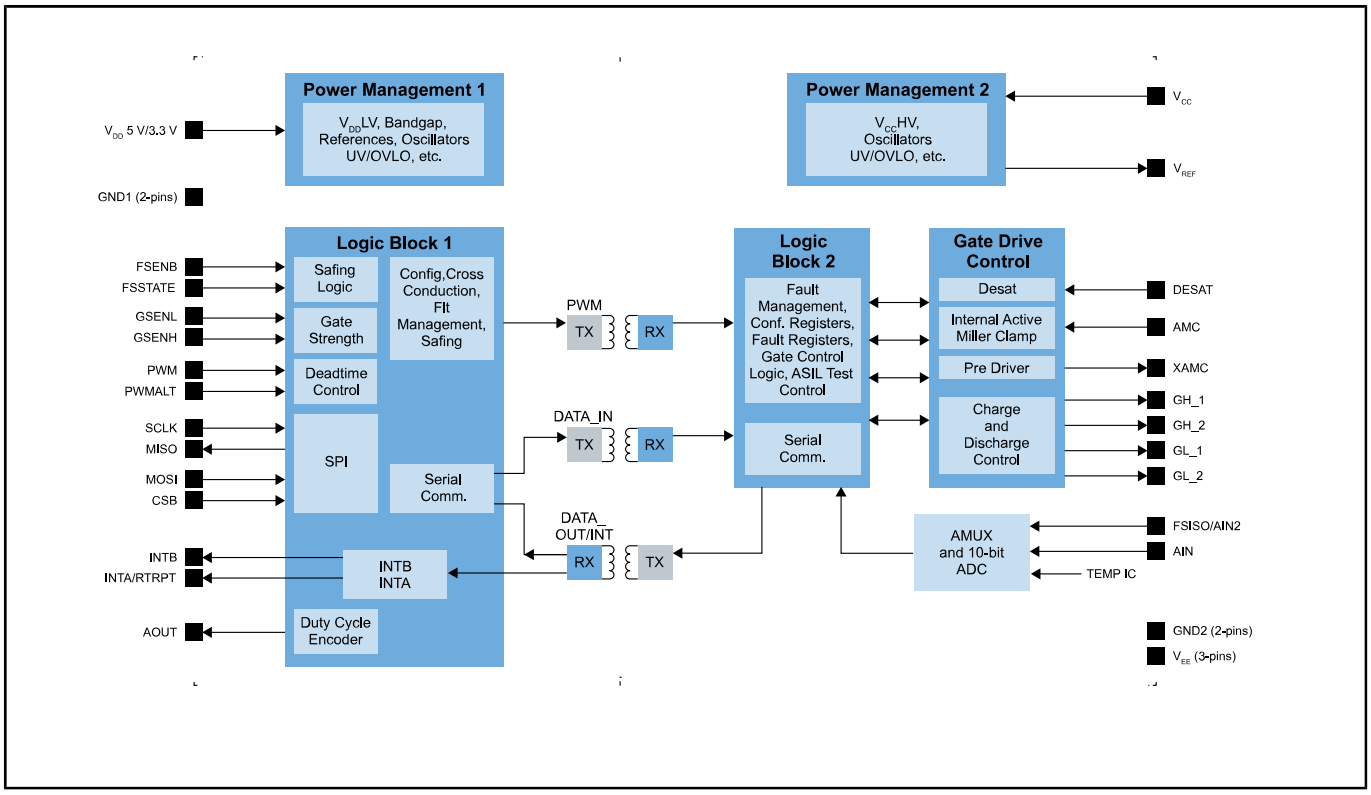
The GD313x/GD312x family consists of a galvanically isolated, single-channel gate driver designed for silicon carbide (SiC) metal-oxide-semiconductor field-effect transistor (MOSFET) and insulated-gate bipolar transistor (IGBT) power modules in xEV traction inverter applications. These devices integrate galvanic isolation, a serial peripheral interface (SPI)-programmable, advanced protection features and boost capability for directly driving the gate..

The devices autonomously detect and manage faults and provide configurable VCE/VDS and VGE monitoring for enhanced diagnostics. Built-in self-test (BIST) functions and protection features support the development of systems targeting ASIL C and ASIL D functional safety requirements. The GD313x/2x is AEC-Q100 Grade 1 qualified for automotive applications. The GD313x also provides adjustable dynamic gate strength.

GD3120 Block Diagram



GD3130 Block Diagram



View additional information for GD313x/GD312x Advanced High Voltage Isolated Gate Driver.

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